

Green LED Chip

SL-NGIP0200-[V#W#I#]

- MOVPE epi-wafer of InGaN alloy films
- Normal type chip (brightness enhanced with patterned substrate)
- ※ All samples are 100% tested and sorted, and user can consult about special specifications.

■ ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

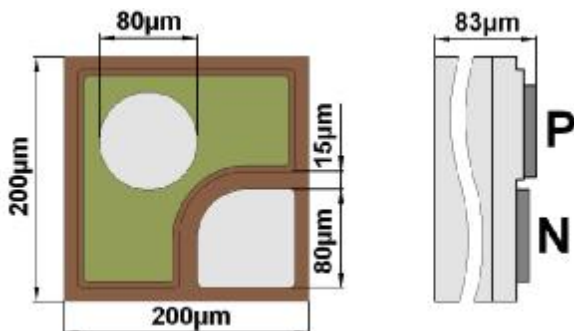
Item	Symbol	Maximum Rating	Unit
DC Forward Current	I_F	30	mA
Pulse Forward Current	I_{FP}	100	mA
Reverse Voltage	V_R	10	V
Operating Temperature	T_{opr}	-30 to +85	°C
Storage Temperature	T_{stg}	-40 to +100	°C
ESD sensitivity (HBM) *	V_{ESDS}	2000	V

*2000V ESD testing result is based on statistic measurements and 500V ESD measurement is applied on full testing.

■ OPTICAL AND ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Item	Symbol	Condition		Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=15mA$	V_1	3.0	3.3	3.6	V
Reverse Current	I_R	$V_R=10V$		-	-	0.5	μA
Wavelength	λ_D	$I_F=15mA$	W_1	515	-	517.5	nm
			W_2	517.5	-	520	
			W_3	520	-	522.5	
			W_4	522.5	-	525	
			
			W_7	530	-	532.5	
Luminous Intensity	I_v	$I_F=15mA$	I_1	160	170	180	mcd
			
			I_4	220	230	240	
			I_5	240	250	260	
			I_6	260	270	280	
			I_7	280	290	300	
			

■ CHIP DESCRIPTION



■ MECHANICAL SPECIFICATION

Description	Dimension
Emission Area	180 μm x 180 μm
Bottom Area	200 μm x 200 μm ($\pm 10\mu m$)
Chip Thickness	83 μm ($\pm 5\mu m$)
N-pad	$\Phi=80\mu m$
P-pad	$\Phi=80\mu m$
Electrodes Spacing	15 μm
Electrode material	AL